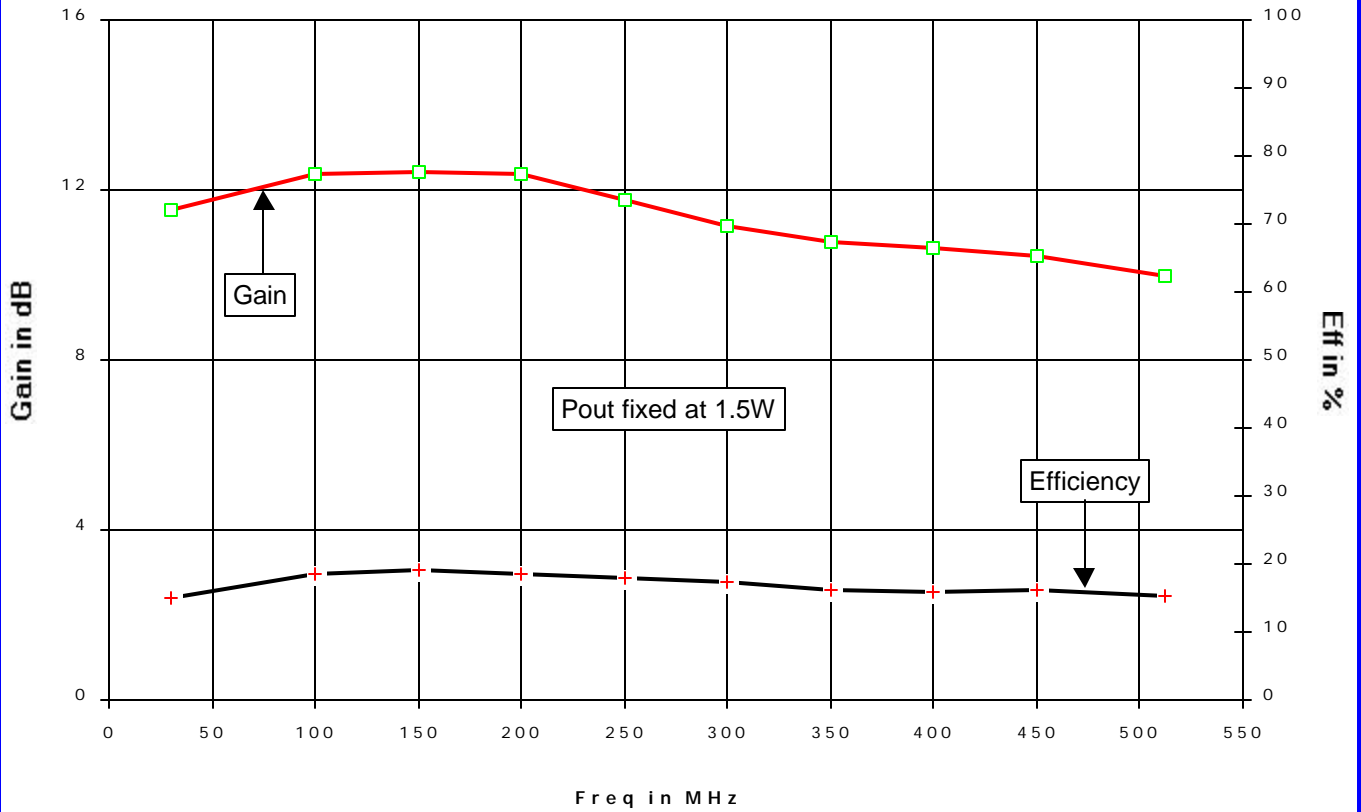
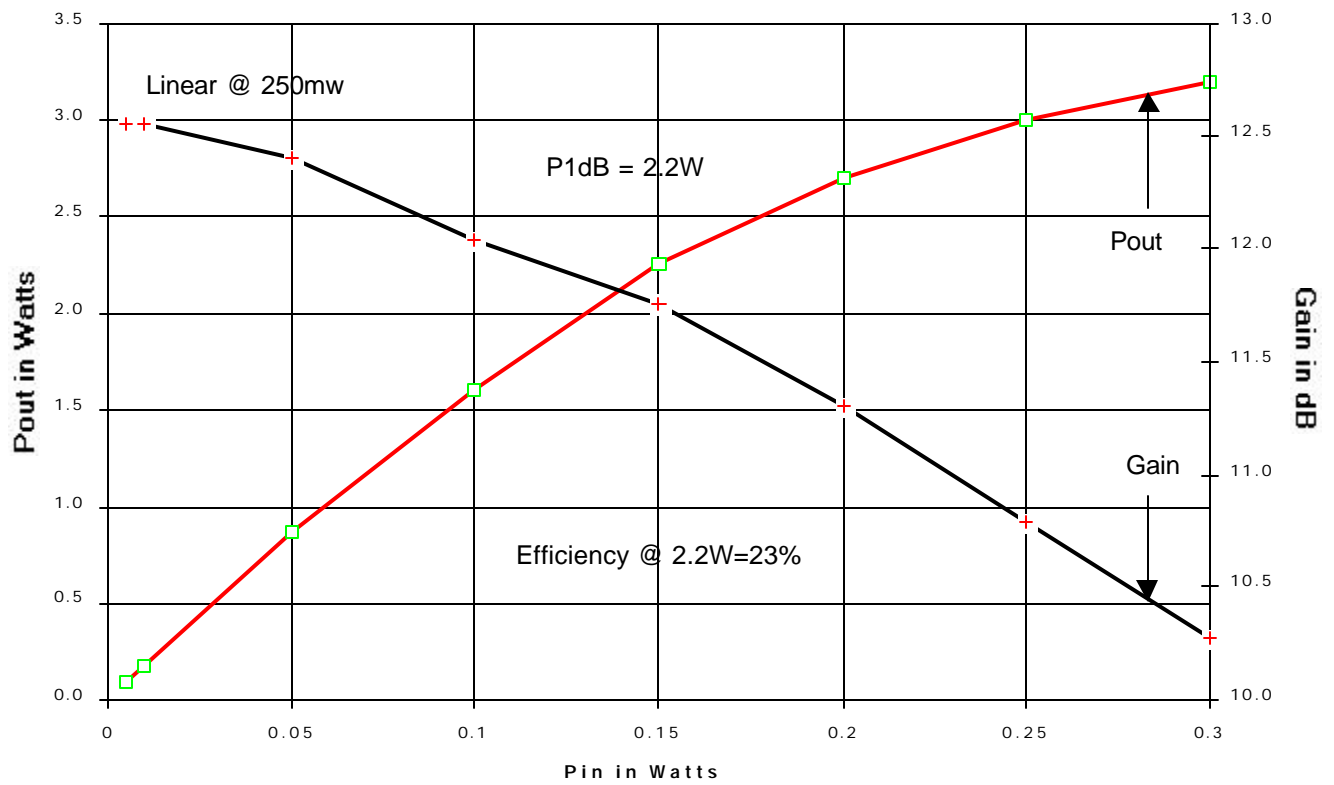
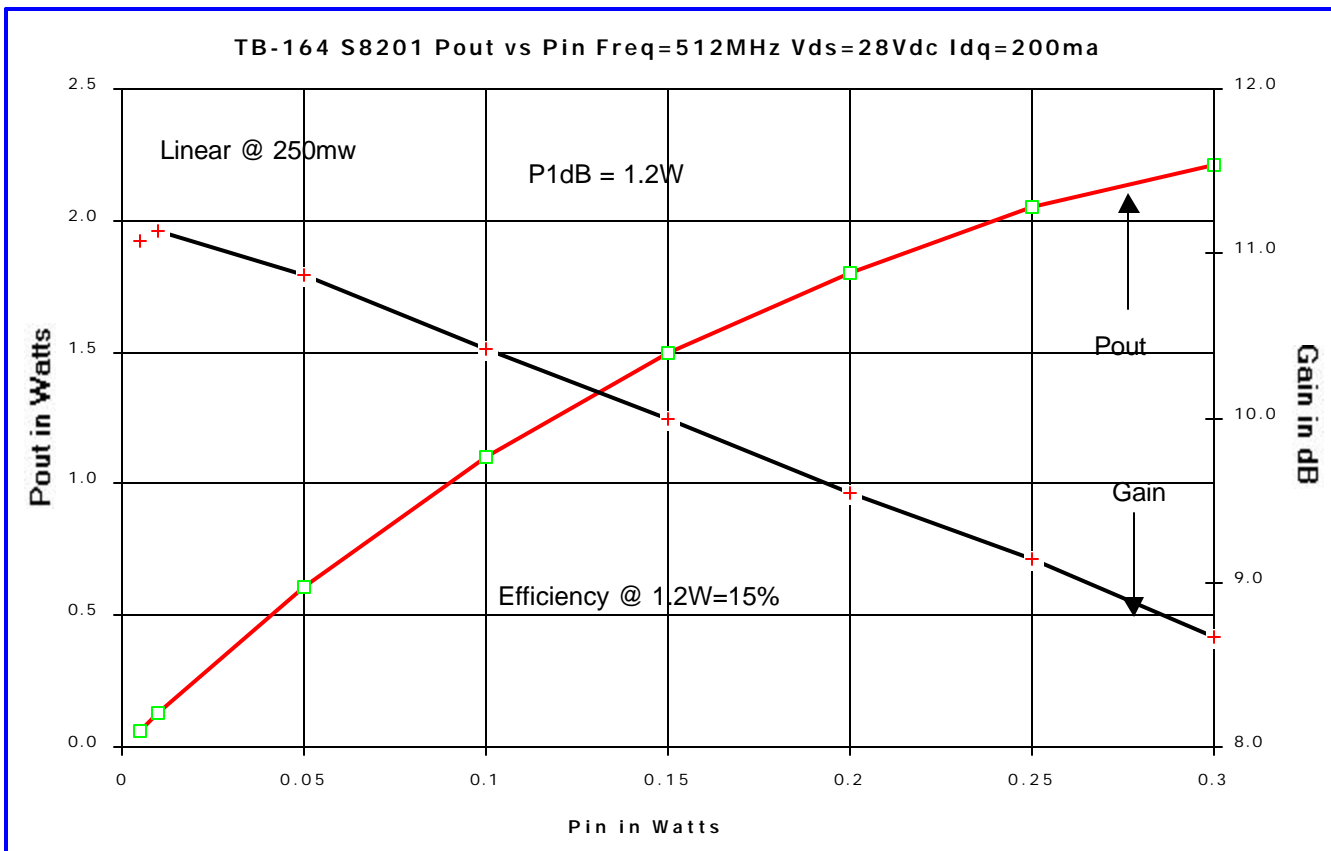
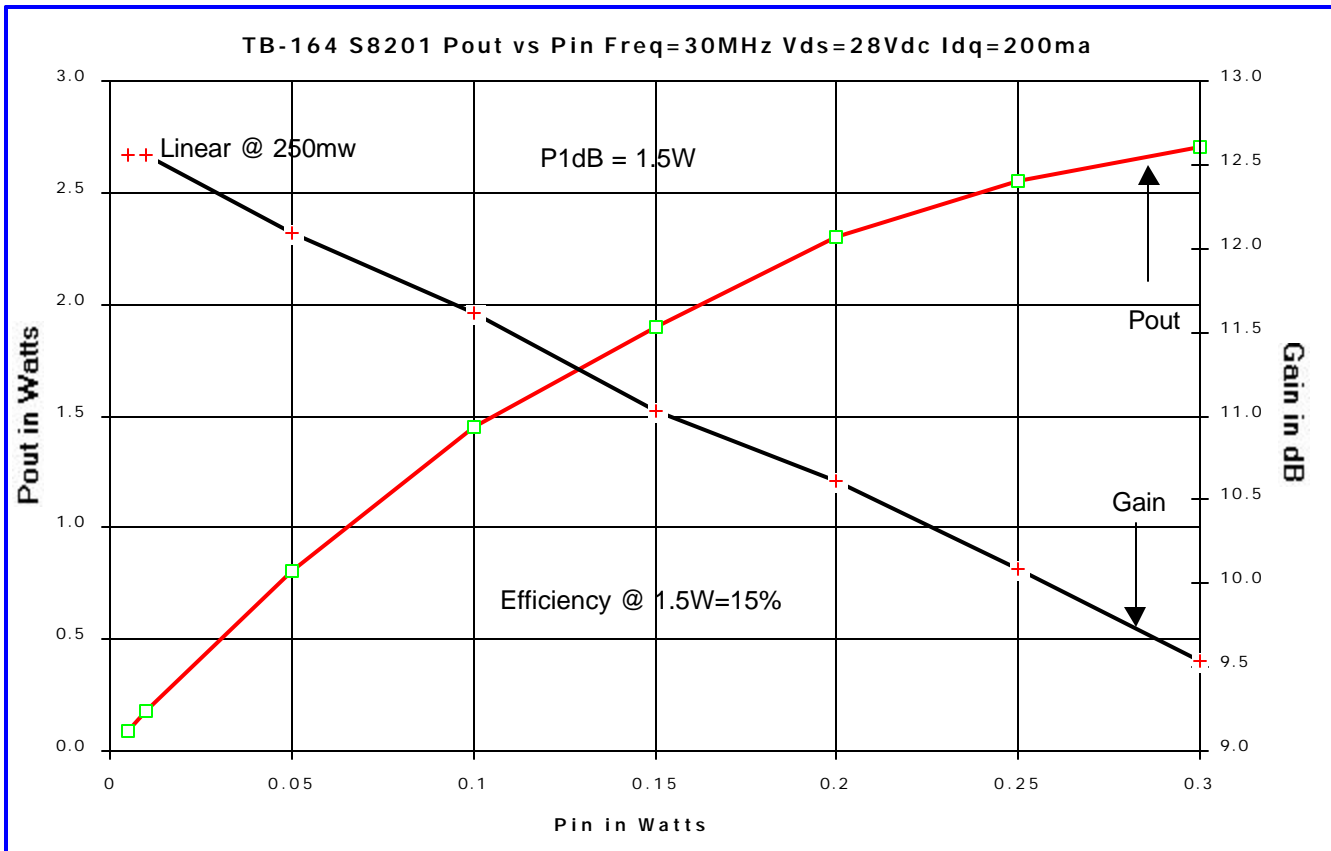


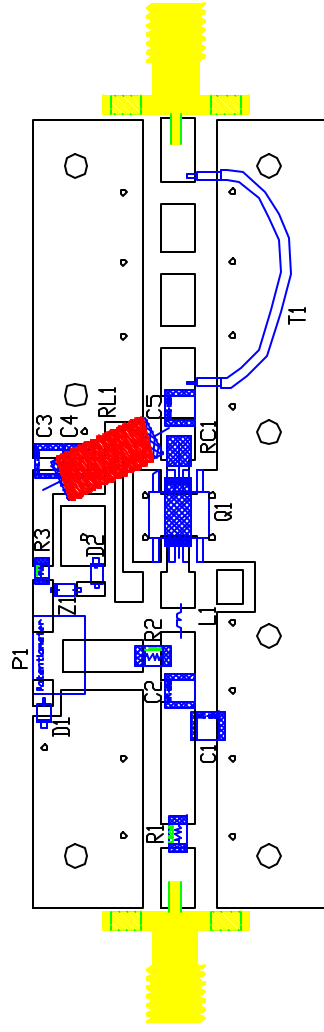
TB-164 S8201 Gain/Efficiency vs Frequency; Vds=28Vdc Idq=.2A



TB-164 S8201 Pout vs Pin Freq=250MHz Vds=28Vdc Idq=200ma





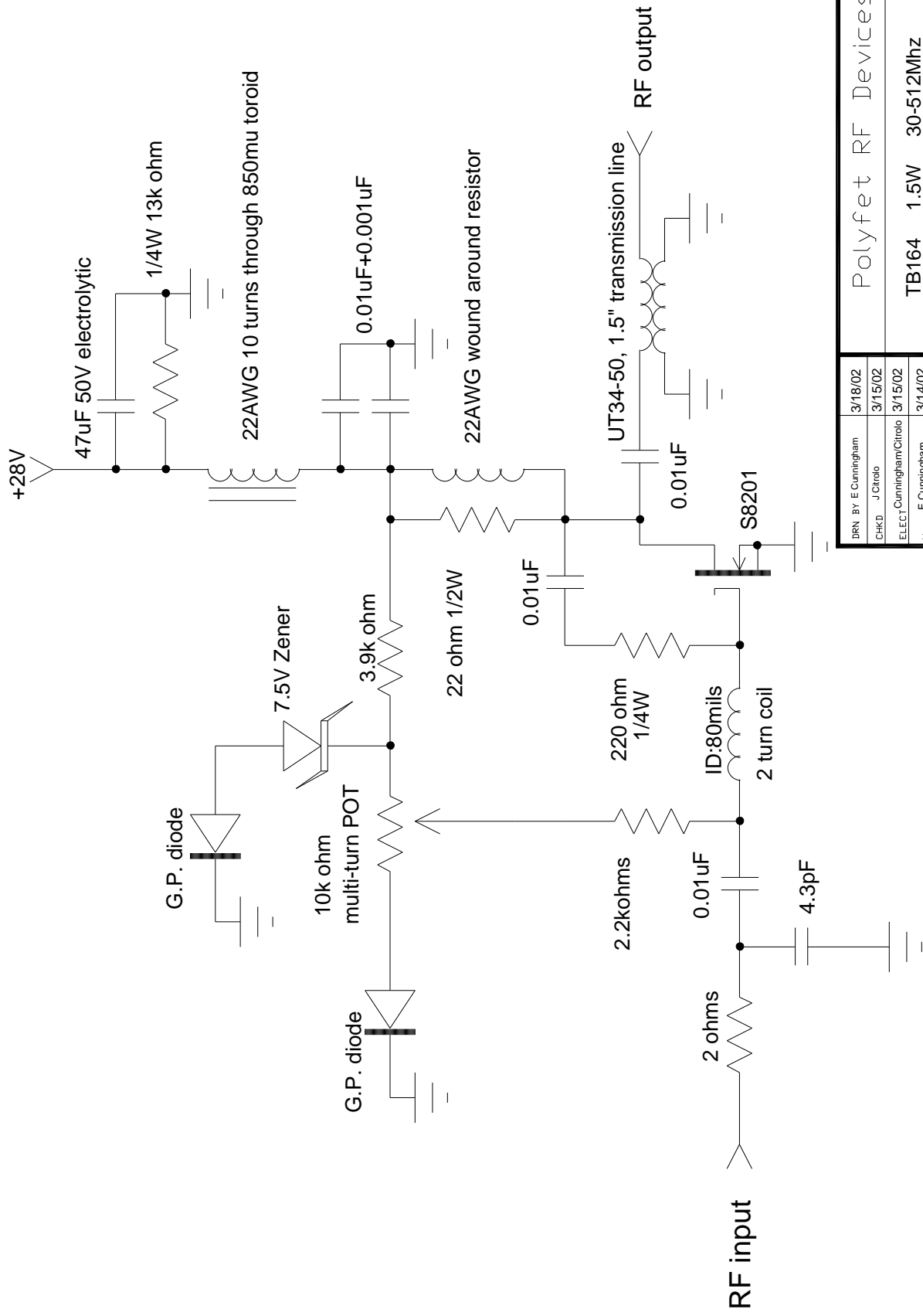


SYMBOL	VALUE	DESCRIPTION
C1	4.3DF	ATC100B CHIP CAP.
C2,C3,C5	0.01uF	ATC100B CHIP CAP.
C4	1000pF	ATC100B CHIP CAP.
R1	2	1206 chip resistor
R2	2.2k	1206 chip resistor
R3	3.9k	0805 chip resistor
P01	10k	multi-turn POT
RL1	22AWG	around 22 ohm 1/2W
RC1	220ohm axial, in series with .01uF ATC100B	
T1	1.5"	UT85-50ohm Coaxial
D1,D2	----	general purpose diode
Z1	7.5V	5mA Zener diode
L1	22AWG	ID:0.08: 2turn coil
Q1	S8201	Polyfet Transistor
VDD	28V	DC Power Supply
Bias	400mA	Bias Current

DESIGNED BY	Cunningham	DATE	9/13/02
DESIGNED	Citrulo/Cunningham	DATE	9/13/02
ELECT	Cunningham	DATE	9/13/02
MECH			
PROC			
DRAWN			
PCBS			

Polyfet RF Devices	
S8201 50-512MHz	
SIZE	SCALE
1:1	1:1
REV	0
TB164 LAYOUT	

PCB Material : Double Side FR4
 ER=3.55, H=0.032", T=0.001"



DRN BY	E Cunningham	3/18/02
CHKD	J Citolo	3/15/02
ELECT	Cunningham/Chitolo	3/15/02
MECH	E Cunningham	3/14/02
PREC		
Q/JAL		
PGMS		

Polyfet RF Devices		
TB164	1.5W	30-512Mhz
SIZE	FSCM NO.	REV
A	S8201	0

